

# N-channel TrenchMOS logic level FET Rev. 02 — 26 April 2011

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

AEC Q101 compliant

Low conduction losses due to low on-state resistance

### **1.3 Applications**

Automotive and general purpose power switching

### 1.4 Quick reference data

#### Table 1. Quick reference data

| Symbol           | Parameter  | Conditions  | Min | Тур  | Max | Unit |
|------------------|--|---|-----|------|-----|------|
| $V_{DS}$         | drain-source voltage                               | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   | -   | -    | 100 | V    |
| I <sub>D</sub>   | drain current                                      | T <sub>mb</sub> = 25 °C   | -   | -    | 49  | А    |
| P <sub>tot</sub> | total power dissipation                            |   | -   | -    | 166 | W    |
| Static cha       | aracteristics                                      |   |     |      |     |      |
| $R_{DSon}$       | drain-source on-state                              | $V_{GS}$ = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C   | -   | 18.5 | 28  | mΩ   |
|                  | resistance   | $V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C  | -   | 17   | 27  | mΩ   |
| Avalanch         | e ruggedness                                       |   |     |      |     |      |
| $E_{DS(AL)S}$    | non-repetitive<br>drain-source<br>avalanche energy | $ \begin{split} I_D &= 30 \text{ A};  \text{V}_{\text{sup}} \leq 25 \text{ V}; \\ \text{R}_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 5 \text{ V}; \\ \text{T}_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $ | -   | -    | 45  | mJ   |



3.

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### 2. Pinning information

| Table 2. | Pinning | information                       |                    |                |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin      | Symbol  | Description                       | Simplified outline | Graphic symbol |
| 1        | G       | gate                              |                    | _              |
| 2        | D       | drain                             | mb                 |                |
| 3        | S       | source                            |                    |                |
| mb       | D       | mounting base; connected to drain |                    | mbb076 S       |

SOT404 (D2PAK)

# Ordering information

| Table 3. Orde | ring information |  |         |
|---------------|------------------|--|---------|
| Type number   | Package          |  |         |
|               | Name             | Description  | Version |
| BUK9628-100A  | D2PAK            | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |

### 4. Limiting values

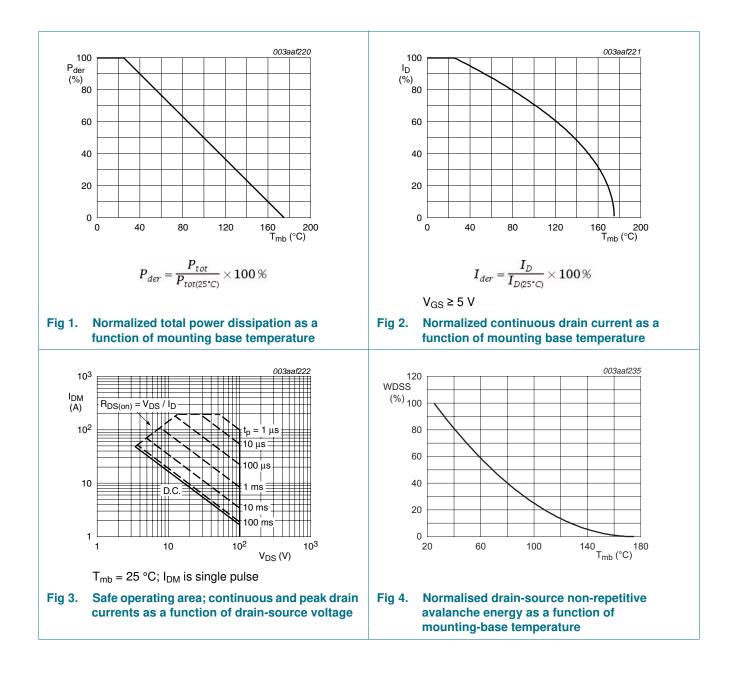
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                       | Conditions  | Min | Max | Unit |
|----------------------|---|---|-----|-----|------|
| V <sub>DS</sub>      | drain-source voltage                            | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   | -   | 100 | V    |
| V <sub>DGR</sub>     | drain-gate voltage                              | $R_{GS} = 20 \text{ k}\Omega$   | -   | 100 | V    |
| V <sub>GS</sub>      | gate-source voltage                             |   | -10 | 10  | V    |
| I <sub>D</sub>       | drain current                                   | T <sub>mb</sub> = 25 °C   | -   | 49  | А    |
|                      |   | $T_{mb} = 100 \ ^{\circ}C$  | -   | 34  | А    |
| I <sub>DM</sub>      | peak drain current                              | T <sub>mb</sub> = 25 °C; pulsed   | -   | 195 | А    |
| P <sub>tot</sub>     | total power dissipation                         | T <sub>mb</sub> = 25 °C   | -   | 166 | W    |
| T <sub>stg</sub>     | storage temperature                             |   | -55 | 175 | °C   |
| Tj                   | junction temperature                            |   | -55 | 175 | °C   |
| V <sub>GSM</sub>     | peak gate-source voltage                        | pulsed; t <sub>p</sub> ≤ 50 μs  | -15 | 15  | V    |
| Source-dra           | ain diode                                       |   |     |     |      |
| ls                   | source current                                  | T <sub>mb</sub> = 25 °C   | -   | 49  | А    |
| I <sub>SM</sub>      | peak source current                             | pulsed; T <sub>mb</sub> = 25 °C   | -   | 195 | А    |
| Avalanche            | ruggedness                                      |   |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche<br>energy | $ \begin{array}{l} I_{D} = 30 \; A; \; V_{sup} \leq 25 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 5 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array} $ | -   | 45  | mJ   |

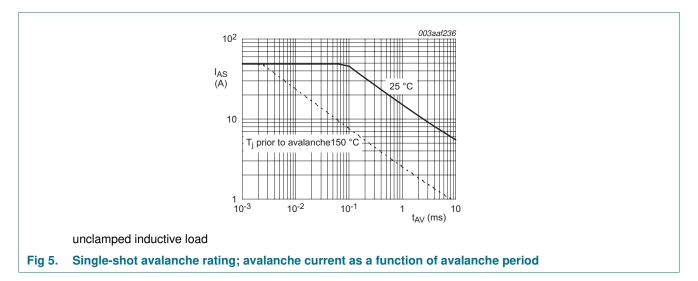
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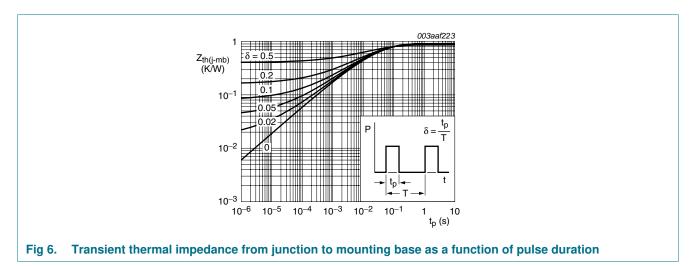
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### 5. Thermal characteristics

#### Table 5.Thermal characteristics

| Symbol               | Parameter  | Conditions                    | Min | Тур | Мах | Unit |
|----------------------|--|-------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$       | thermal resistance from junction to<br>mounting base |                               | -   | -   | 0.9 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient          | minimum footprint ; FR4 board | -   | 50  | -   | K/W  |



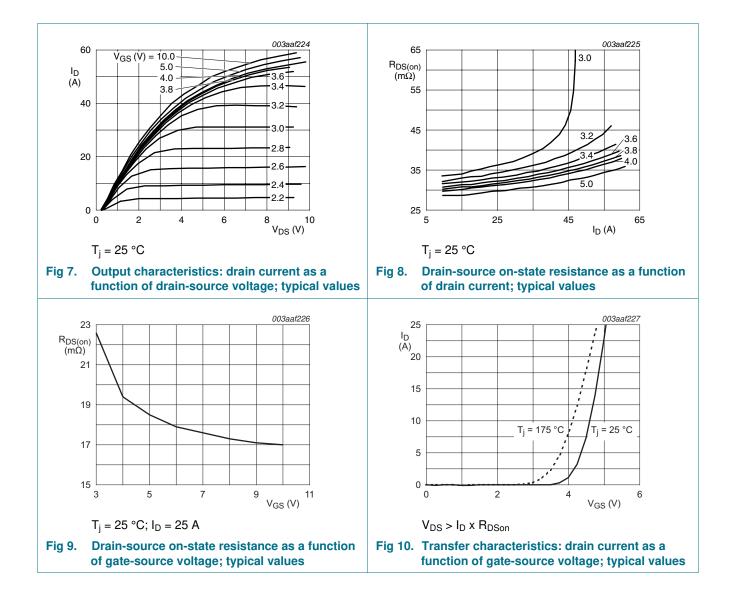
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### 6. Characteristics

| Table 6.             | Characteristics               |   |     |      |      |      |
|----------------------|-------------------------------|---|-----|------|------|------|
| Symbol               | Parameter                     | Conditions  | Min | Тур  | Max  | Unit |
| Static cha           | aracteristics                 |   |     |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source breakdown        | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$                        | 100 | -    | -    | V    |
|                      | voltage                       | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$                       | 89  | -    | -    | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                                | 1   | 1.5  | 2    | V    |
|                      |                               | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$                               | 0.5 | -    | -    | V    |
|                      |                               | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$                               | -   | -    | 2.3  | V    |
| DSS                  | drain leakage current         | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C   | -   | 0.05 | 10   | μA   |
|                      |                               | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C  | -   | -    | 500  | μA   |
| GSS                  | gate leakage current          | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                     | -   | 2    | 100  | nA   |
|                      |                               | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                       | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state         | $V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$       | -   | 18.5 | 28   | mΩ   |
|                      | resistance                    | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C                     | -   | -    | 70   | mΩ   |
|                      |                               | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                     | -   | 17   | 27   | mΩ   |
|                      |                               | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                    | -   | 18.8 | 31   | mΩ   |
| Dynamic              | characteristics               |   |     |      |      |      |
| C <sub>iss</sub>     | input capacitance             | $V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$   | -   | 3220 | 4293 | pF   |
| C <sub>oss</sub>     | output capacitance            | T <sub>j</sub> = 25 °C  | -   | 315  | 378  | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance  |   | -   | 187  | 256  | pF   |
| t <sub>d(on)</sub>   | turn-on delay time            | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$        | -   | 11   | 16   | ns   |
| t <sub>r</sub>       | rise time                     | $R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$  | -   | 58   | 87   | ns   |
| t <sub>d(off)</sub>  | turn-off delay time           |   | -   | 250  | 350  | ns   |
| t <sub>f</sub>       | fall time                     |   | -   | 106  | 148  | ns   |
| L <sub>D</sub>       | internal drain inductance     | measured from drain lead 6 mm from package to centre of die ; $T_j = 25 ^{\circ}\text{C}$ | -   | 4.5  | -    | nH   |
|                      |                               | measured from upper edge of drain tab to centre of die ; $T_j = 25 \text{ °C}$            | -   | 2.5  | -    | nH   |
| -s                   | internal source inductance    | measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$                      | -   | 7.5  | -    | nH   |
| Source-d             | rain diode                    |   |     |      |      |      |
| V <sub>SD</sub>      | source-drain voltage          | $I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$                       | -   | 0.85 | 1.2  | V    |
|                      |                               | $I_{S} = 49 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$                       | -   | 1.1  | -    | V    |
| t <sub>rr</sub>      | reverse recovery time         | $I_{S} = 49 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$            | -   | 63   | -    | ns   |
| Q <sub>r</sub>       | recovered charge              | $V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C  | -   | 0.22 | -    | μC   |

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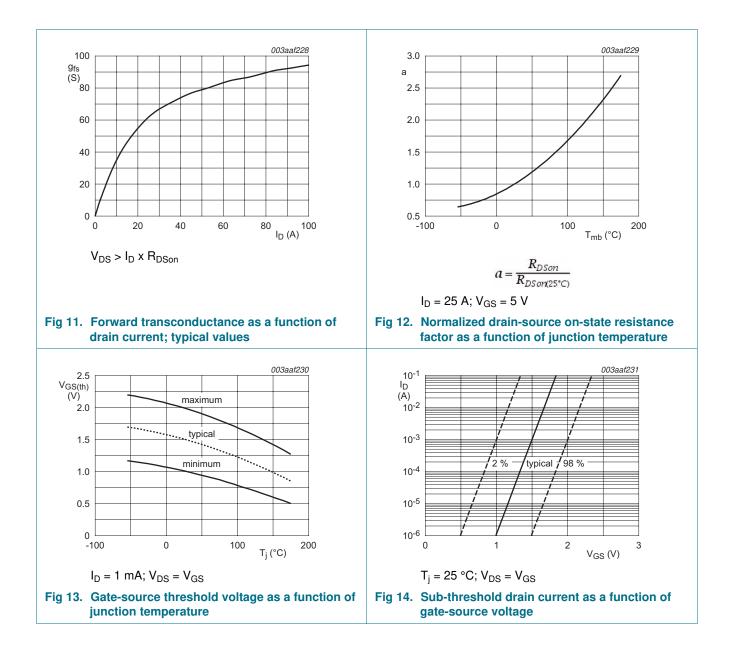
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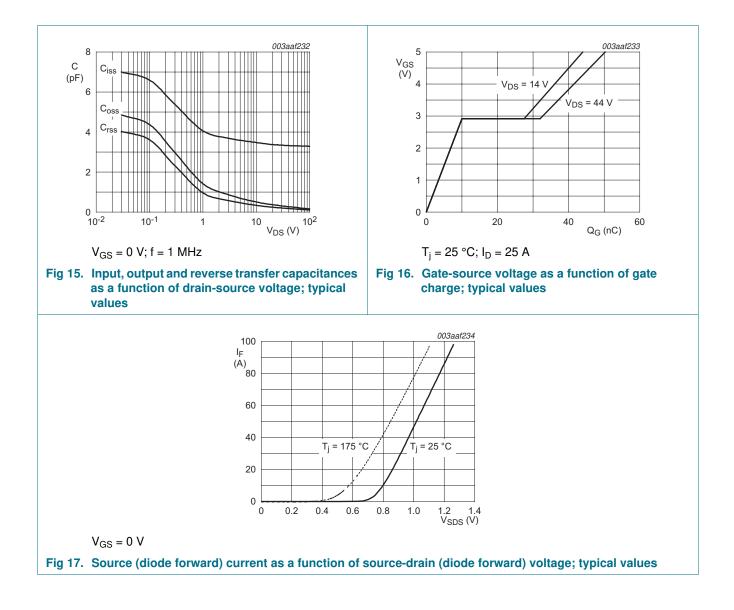
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#### **Package outline** 7.

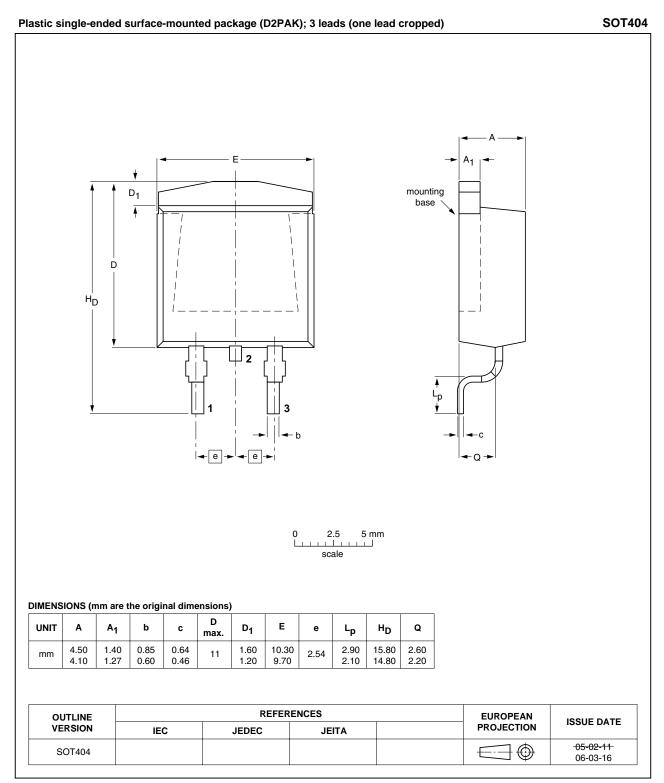


Fig 18. Package outline SOT404 (D2PAK)

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### 8. Revision history

| Table 7.       | <b>Revision history</b> |   |   |                  |                       |
|----------------|-------------------------|---|---|------------------|-----------------------|
| Document       | ID                      | Release date  | Data sheet status   | Change notice    | Supersedes            |
| BUK9628-1      | 00A v.2                 | 20110426  | Product data sheet  | -                | BUK9528_9628-100A v.1 |
| Modifications: |                         | guidelines of l <ul> <li>Legal texts has</li> </ul> | this data sheet has been<br>NXP Semiconductors.<br>ave been adapted to the r<br>BUK9628-100A separate | new company name |                       |
| BUK9528_       | 9628-100A v.1           | 20000301  | Product specification   | -                | -                     |

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### 9.1 Data sheet status

| Document status [1] [2]        | Product status 3 | Definition  |
|--------------------------------|------------------|---|
| Objective [short] data sheet   | Development      | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification    | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production       | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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